BSZ120P03NS3EGATMA1-VB Datasheet

P-Channel 30-V (D-S) MOSFET

V_{DS}		-30	V
$R_{DS(on),typ}$	V_{GS}=10V	9	mΩ
$R_{DS(on),typ}$	V_{GS}=4.5V	17	mΩ
I_D		-30	A

FEATURES

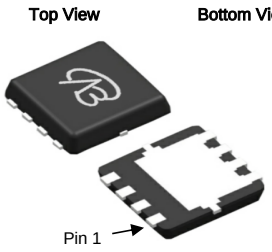
- Trench power MOSFET
- 100 % R_g and UIS tested

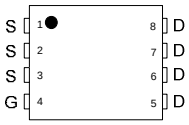
APPLICATIONS

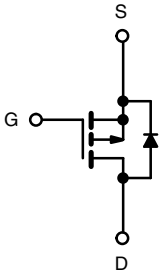
- Notebook battery charging
- Notebook adapter switch

RoHS COMPLIANT
HALOGEN FREE

DFN 3x3







P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
PARAMETER		**SYMBOL**	**LIMIT**	**UNIT**
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 25	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	-30 [d]	A
	T_C = 70 °C		-25 [d]	
	T_A = 25 °C		-13.9 [a, b]	
	T_A = 70 °C		-11.1 [a, b]	
Pulsed Drain Current		I_{DM}	-120	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	-35 [d]	
	T_A = 25 °C		-3 [a, b]	
Avalanche Current	L = 0.1 mH	I_{AS}	-29	
Single-Pulse Avalanche Energy		E_{AS}	42	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	52	W
	T_C = 70 °C		33	
	T_A = 25 °C		3.7 [a, b]	
	T_A = 70 °C		2.4 [a, b]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +150	°C
Soldering Recommendations (Peak Temperature) [e, f]			260	

THERMAL RESISTANCE RATINGS					
PARAMETER		**SYMBOL**	**TYPICAL**	**MAXIMUM**	**UNIT**
Maximum Junction-to-Ambient [a, c]	t ≤ 10 s	R_{thJA}	26	33	°C/W
Maximum Junction-to-Case	Steady State	R_{thJC}	1.9	2.4	

Notes

a. Surface mounted on 1" x 1" FR4 board.
b. t = 10 s.
c. Maximum under steady state conditions is 81 °C/W.
d. Package limited.
e. The DFN 3 x 3 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
g. Based on T_C = 25 °C.

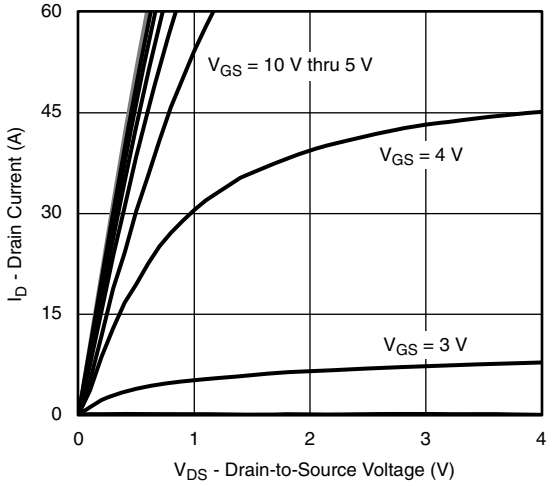
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = -250 µA	-30	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = -250 µA	-	-25	-	mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		-	4.7	-	
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 µA	-1.2	-	-2.5	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 25 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -30 V, V_{GS} = 0 V	-	-	-1	µA
		V_{DS} = -30 V, V_{GS} = 0 V, T_J = 55 °C	-	-	-5	
On-State Drain Current [a]	$I_{D(on)}$	V_{DS} ≥ -10 V, V_{GS} = -10 V	-30	-	-	A
Drain-Source On-State Resistance [a]	$R_{DS(on)}$	V_{GS} = -10 V, I_D = -13.9 A	-	9	-	mΩ
		V_{GS} = -4.5 V, I_D = -10.3 A	-	17	-	
Forward Transconductance [a]	g_{fs}	V_{DS} = -15 V, I_D = -13.9 A	-	35	-	S
Dynamic [b]						
Input Capacitance	C_{iss}	V_{DS} = -15 V, V_{GS} = 0 V, f = 1 MHz	-	1800	-	pF
Output Capacitance	C_{oss}		-	370	-	
Reverse Transfer Capacitance	C_{rss}		-	312	-	
Total Gate Charge	Q_g	V_{DS} = -15 V, V_{GS} = -10 V, I_D = -13.9 A	-	-	15	nC
		V_{DS} = -15 V, V_{GS} = -4.5 V, I_D = -13.9 A	-	-	13	
Gate-Source Charge	Q_{gs}		-	-	6	
Gate-Drain Charge	Q_{gd}		-	-	11	
Gate Resistance	R_g	f = 1 MHz	0.4	2	4	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -15 V, R_L = 1.35 Ω I_D ≅ -11.1 A, V_{GEN} = -10 V, R_g = 1 Ω	-	11	22	ns
Rise Time	t_r		-	9	18	
Turn-Off DelayTime	$t_{d(off)}$		-	32	50	
Fall Time	t_f		-	9	18	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -15 V, R_L = 1.35 Ω I_D ≅ -11.1 A, V_{GEN} = -4.5 V, R_g = 1 Ω	-	40	60	
Rise Time	t_r		-	43	65	
Turn-Off DelayTime	$t_{d(off)}$		-	30	45	
Fall Time	t_f		-	11	22	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C	-	-	-35	A
Pulse Diode Forward Current	I_{SM}		-	-	-60	
Body Diode Voltage	V_{SD}	I_S = -11.1 A, V_{GS} = 0 V	-	-0.8	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = -11.1 A, dI/dt = 100 A/µs, T_J = 25 °C	-	33	50	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	30	45	nC
Reverse Recovery Fall Time	t_a		-	18	-	ns
Reverse Recovery Rise Time	t_b		-	16	-	

Notes

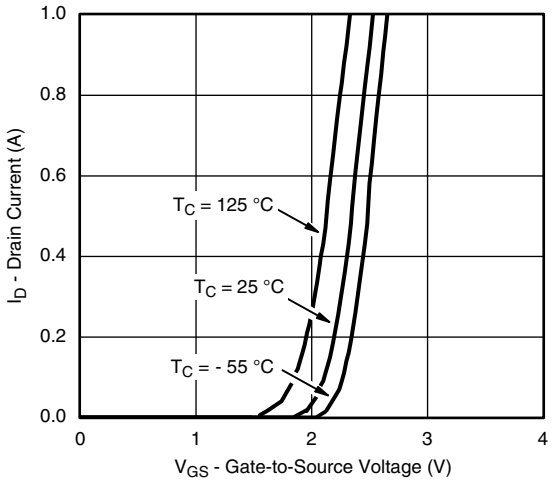
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

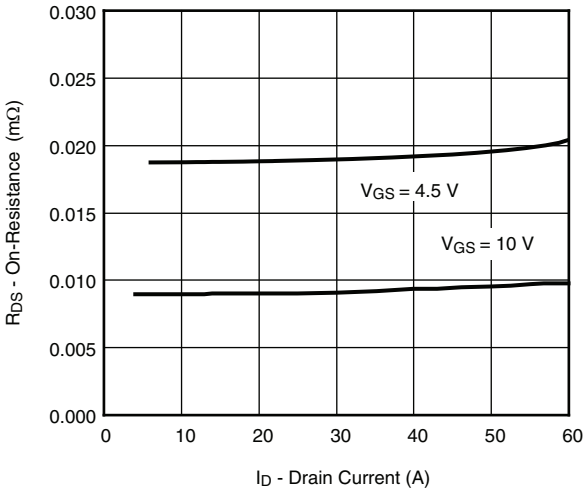
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



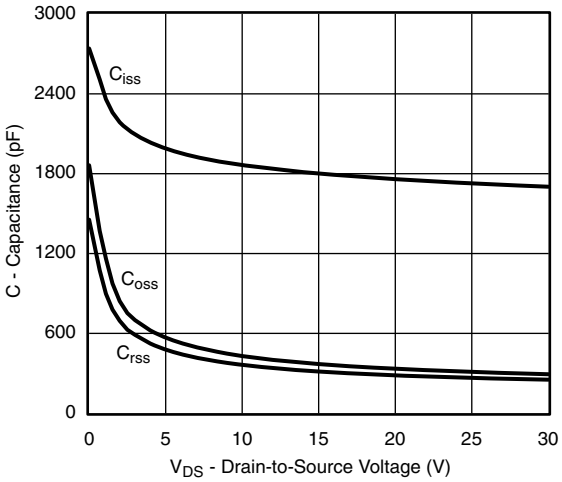
Output Characteristics



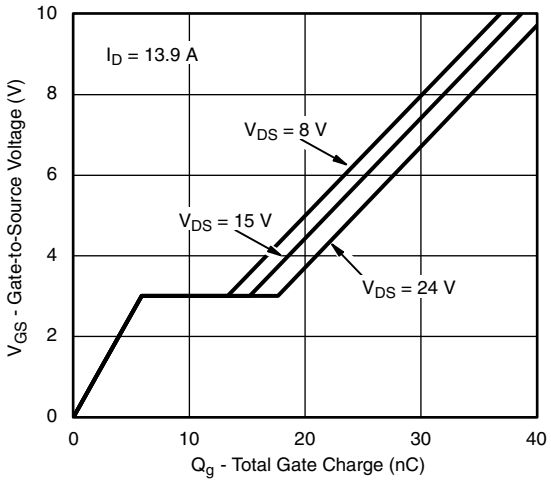
Transfer Characteristics



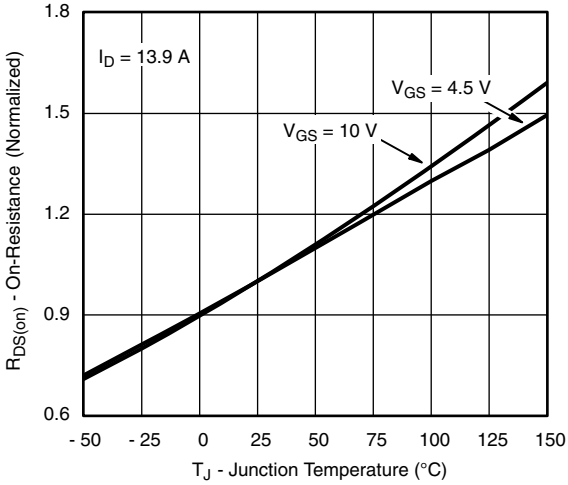
On-Resistance vs. Drain Current



Capacitance

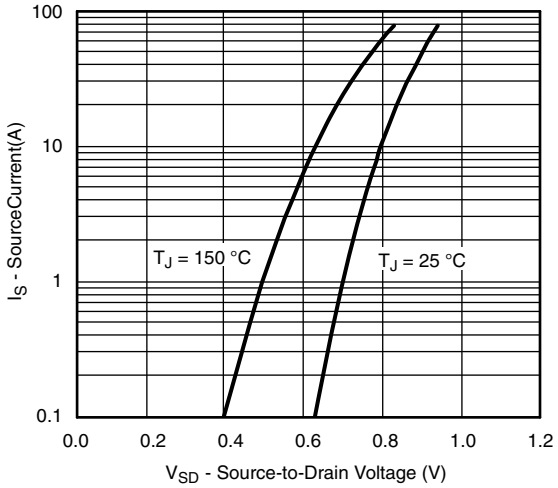


Gate Charge

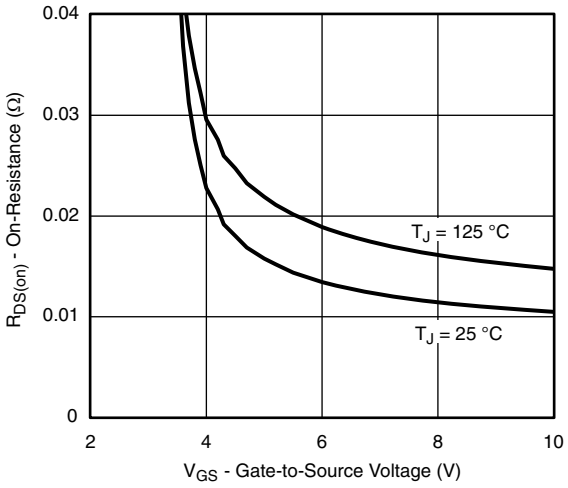


On-Resistance vs. Junction Temperature

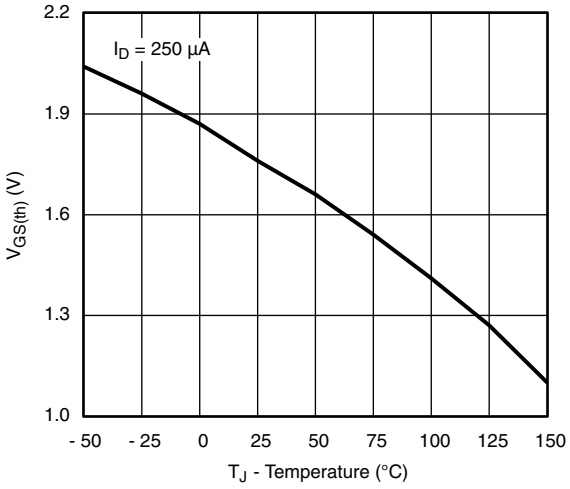
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



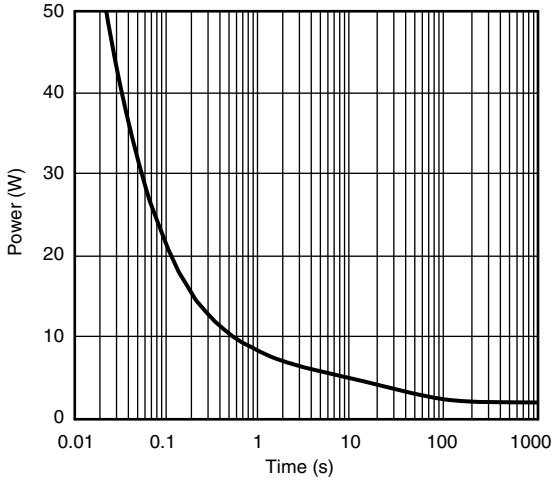
Source-Drain Diode Forward Voltage



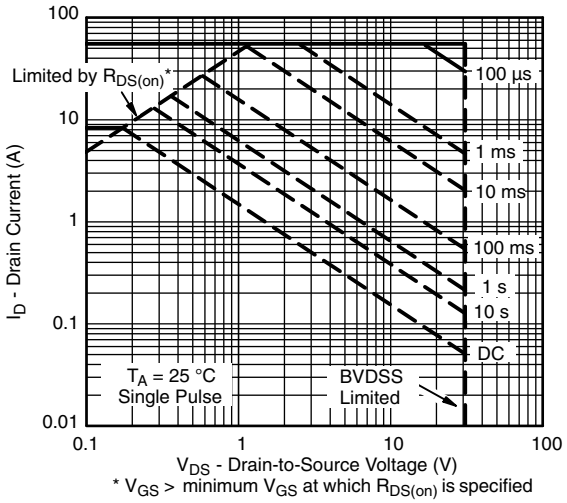
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

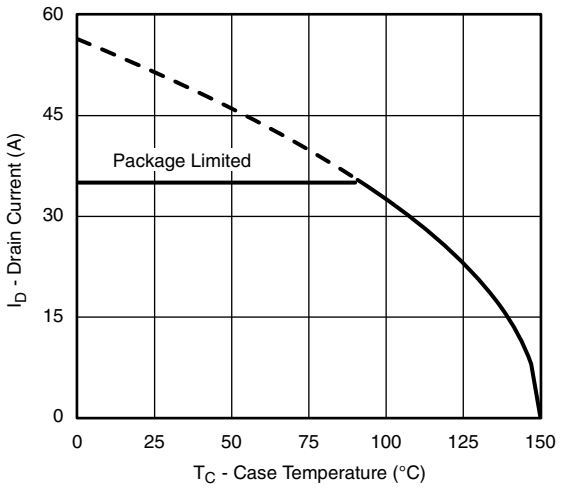


Single Pulse Power, Junction-to-Ambient

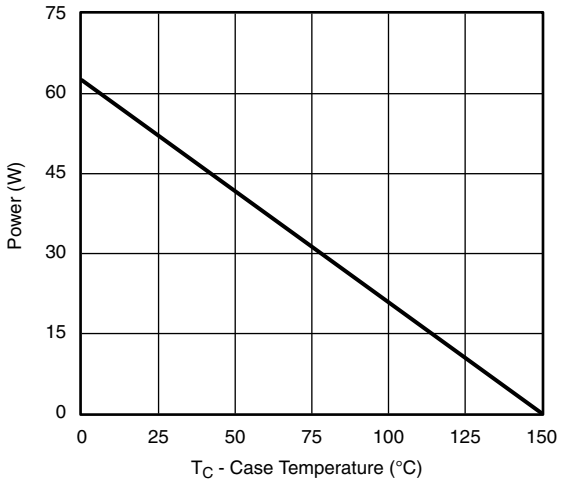


Safe Operating Area

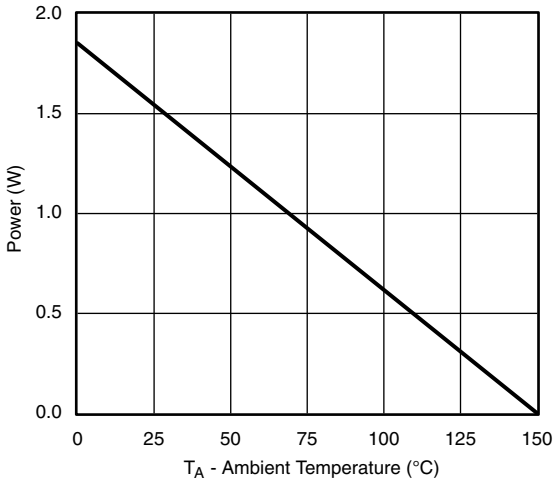
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



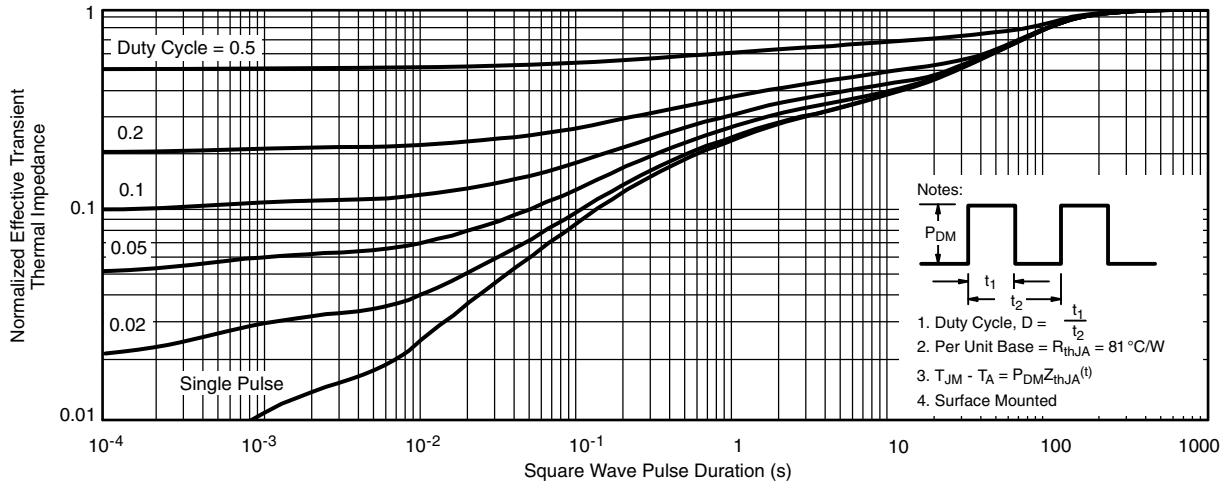
Power Derating, Junction-to-Case



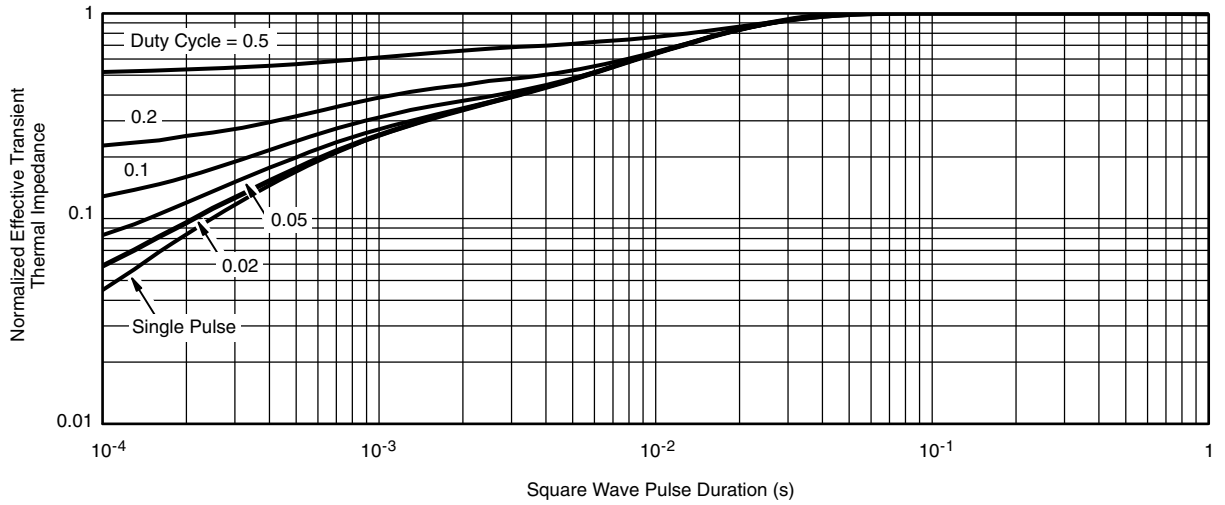
Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on T_J (max.) = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

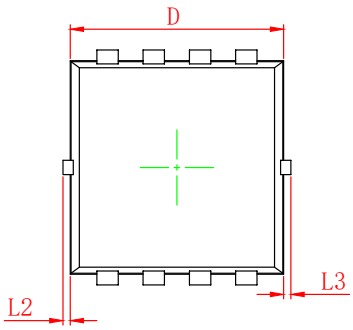


Normalized Thermal Transient Impedance, Junction-to-Ambient

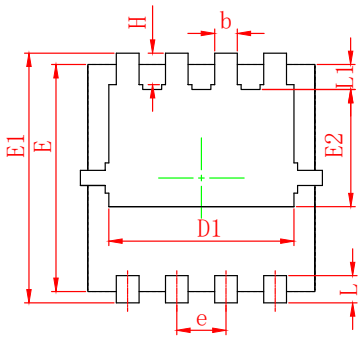


Normalized Thermal Transient Impedance, Junction-to-Case

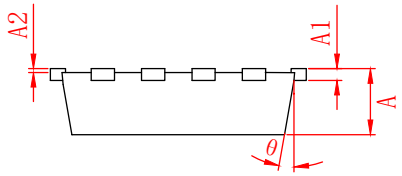
PDFNWB3×3-8L Package Outline Dimensions



Top View
[顶视图]



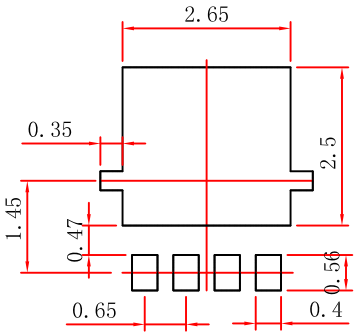
Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.650	0.850	0.026	0.033
A1	0.203REF.		0.008REF.	
A2	0~0.05		0~0.002	
D	2.900	3.100	0.114	0.122
D1	2.050	2.550	0.081	0.100
E	2.900	3.100	0.114	0.122
E1	3.150	3.450	0.124	0.136
E2	1.450	1.650	0.057	0.065
b	0.200	0.400	0.008	0.016
e	0.550	0.750	0.022	0.030
L	0.300	0.500	0.012	0.020
L1	0.180	0.480	0.007	0.019
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.315	0.515	0.012	0.020
Φ	9°	13°	9°	13°

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.

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